ı	
4	

L Number	Hits	Search Text	I DB	Time stamp
1	149	· · · · · · · · · · · · · · · · · · ·	USPAT	2002/05/16 18:25
-	117	(CF4 or tetrafluoromethane) and (O2 or		2002,00,10 20120
2	140	oxygen) ((("TiN") or (titanium adj nitride)) and	USPAT	2002/05/16 18:07
2	149	((CF4 or tetrafluoromethane) and (O2 or	USPAI	2002/03/16 16:07
		oxygen)) and (etch\$3 or pattern\$3 or		
		defin\$3 or form\$3)		
3	140	((("TiN") or (titanium adj nitride)) and	USPAT	2002/05/16 18:08
		(CF4 or tetrafluoromethane) and (O2 or oxygen)) and (etch\$3 or pattern\$3 or		
		defin\$3)		
4	235	(("TiN") or (titanium adj nitride) or	USPAT	2002/05/16 18:08
		barrier or etch\$1stop) and (CF4 or		
_	010	tetrafluoromethane) and (O2 or oxygen)		0000/05/16 10 00
5	219	((("TiN") or (titanium adj nitride) or barrier or etch\$1stop) and (CF4 or	USPAT	2002/05/16 18:08
		tetrafluoromethane) and (O2 or oxygen))		
		and (etch\$3 or pattern\$3 or defin\$3)		
6	45	(titanium adj nitride) and (CF4 or	USPAT	2002/05/16 18:25
	1560	tetrafluoromethane) and (O2 or oxygen)		0000/05/16 10 00
7	1568	(titanium adj nitride) and (silicon adj carbide)	USPAT	2002/05/16 18:20
8	126	((titanium adj nitride) and (silicon adj	USPAT	2002/05/16 18:21
-		carbide)) and (barrier adj layer)		
9	9	((titanium adj nitride) and (silicon adj	USPAT	2002/05/16 18:24
1.0	<b>5</b> 1	carbide)) and (etch\$1stop adj layer)		0000/05/16 10 05
10	51	(SiC or (Silicon adj carbide)) and (CF4 or tetrafluoromethane) and (O2 or oxygen)	USPAT	2002/05/16 18:27
11	570	((SiC or (Silicon adj carbide))near\$4	USPAT	2002/05/16 18:28
	0,0	etch\$3) and (CF4 or tetrafluoromethane)		2002,00,10 10.20
		and (O2 or oxygen)		
12	313	((SiC or (Silicon adj carbide))near\$4	USPAT	2002/05/16 18:30
		etch\$3) and (CF4 or tetrafluoromethane) and (O2 or oxygen) and (ar or argon)		
13	916094		USPAT	2002/05/16 18:32
		etch\$3)		
14	313	(((SiC or (Silicon adj carbide))near\$4	USPAT	2002/05/16 18:34
		etch\$3) ) and (CF4 or tetrafluoromethane)		
15	37675	and (O2 or oxygen) and (ar or argon) (SiC or (Silicon adj carbide))	USPAT	2002/05/16 18:42
16	916094	((SiC or (Silicon adj carbide))) near\$4	USPAT	2002/05/16 18:34
		etch\$3		
17	883749	((SiC or (Silicon adj carbide))) near\$2	USPAT	2002/05/16 18:34
1.0	210	etch\$3	HCDAM	2002/05/16 18:41
18	312	(((SiC or (Silicon adj carbide))) near\$2 etch\$3) and (CF4 or tetrafluoromethane)	USPAT	2002/05/16 18:41
		and (O2 or oxygen) and (ar or argon)		
19	239	((((SiC or (Silicon adj carbide))) near\$2	USPAT	2002/05/16 18:36
		etch\$3) and (CF4 or tetrafluoromethane)	-	
		and (O2 or oxygen) and (ar or argon)) and substrate		
20	27	(((((SiC or (Silicon adj carbide))) near\$2	USPAT	2002/05/16 18:37
		etch\$3) and (CF4 or tetrafluoromethane)		
		and (O2 or oxygen) and (ar or argon)) and		
		substrate) and (SiC or (Silicon adj		
21	108	carbide)) (((SiC or (Silicon adj carbide))) near\$2	USPAT	2002/05/16 19:00
	100	etch\$3) and (CH2f2 or difluoromethane) and		2552,55,15 15.00
		(O2 or oxygen) and (ar or argon)	1	
22	53	((((SiC or (Silicon adj carbide))) near\$2	USPAT	2002/05/16 18:42
		etch\$3) and (CH2f2 or difluoromethane) and		
		(O2 or oxygen) and (ar or argon)) and substrate		
23	12		USPAT	2002/05/16 18:45
		etch\$3) and (CH2f2 or difluoromethane) and		
] [		(02 or oxygen) and (ar or argon)) and		
		substrate) and (SiC or (Silicon adj   carbide))		
24	37675	(SiC or (Silicon adj carbide))	USPAT	2002/05/16 18:45
	3.0.3	, , = = = = , = = = = = = = = = = = = =	1 201111	1 2002/00/10 10.40

25	14	((SiC or (Silicon adj carbide))) and	USPAT	2002/05/16 18:49
25	14	(CH2f2 or difluoromethane) and (O2 or	USERI	2002/03/10 10:43
		oxygen) and (ar or argon)		
26	195		USPAT	2002/05/16 18:50
26	195		USFAI	2002/03/10 10:30
•		oxygen) and (ar or argon) and (n2 or nitrogen)		
27	37	, , , , , , , , , , , , , , , , , , ,	USPAT	2002/05/16 18:51
21	37	, , , , , , , , , , , , , , , , , , , ,	USFAI	2002/03/10 18.31
		oxygen) and (ar or argon) and (n2 or		
0.0	10	nitrogen) ) and strip\$4	USPAT	2002/05/16 18:59
28	10	','	USPAI	2002/03/10 18.39
		oxygen) and (ar or argon) and (n2 or		
		nitrogen) ) and strip\$4) and (resist or		
29	44499	photo\$1resist or photo\$polymer)   (resist or photo\$1resist or photo\$polymer)	USPAT	2002/05/16 19:00
29	44499	and strip\$4	USFAI	2002/05/10 19:00
30	1142619	)	USPAT	2002/05/16 19:01
30	1142019	near\$2 strip\$4	USERI	2002/05/10 15:01
31	123	1 '	USPAT	2002/05/16 19:02
31	123	photo\$polymer) near\$2 strip\$4 ) and (CH2f2	USIAI	2002/03/10 13:02
		or difluoromethane) and (O2 or oxygen) and		
		(ar or argon)		-
32	8066		USPAT	2002/05/16 19:01
32	8000	near2 strip\$4	ODIAI	2002/03/10 13:01
33	8	1	USPAT	2002/05/16 19:05
33	0	photo\$polymer) near2 strip\$4 ) and (CH2f2	ODIAI	2002,03,10 13.03
		or difluoromethane) and (O2 or oxygen) and		
		(ar or argon)		],
34	5	1 '	USPAT	2002/05/16 19:06
73		photo\$polymer) near2 strip\$4 ) and (CH2f2	322	2002, 00, 10 13.00
		or difluoromethane) and (O2 or oxygen) and		
		(ar or argon) and (n2 or nitrogen)		
	1	(at of argon) and (ne of nicrogen)	1	